

关键参数 Key Parameters

| | | | |
|---------------|------|------|---|
| V_{CES} | | 750 | V |
| $V_{CE(sat)}$ | Typ. | 1.25 | V |
| I_C | Max. | 820 | A |
| $I_{C(RM)}$ | Max. | 1640 | A |

典型应用 Typical Applications

| | |
|-------------|----------------------------|
| ● 电动汽车 | Automotive Applications |
| ● 混合动力/纯电动车 | Hybrid/Electrical Vehicles |
| ● 电机驱动 | Motor Drives |

特点 Features

| | |
|-------------|-----------------------|
| ● 铜针翅基板 | Cu pin-fin Baseplate |
| ● 低开关损耗 | Low Switching Losses |
| ● 750V 额定电压 | Blocking Voltage 750V |
| ● 低感设计 | Low Inductive Design |

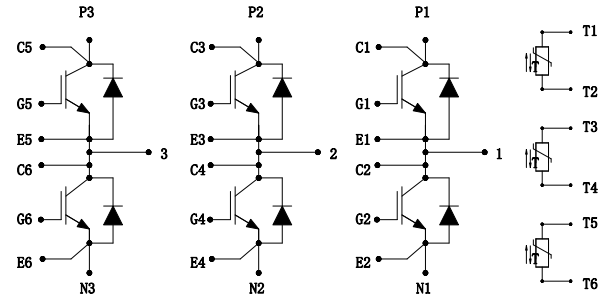
电路结构 Circuit Configuration


图 1. 电路结构

Fig. 1 Circuit configuration

模块外形 Module Appearance


图 2. 模块外形

Fig. 2 Module appearance

模块标签说明

Module Label Code Instruction

| 数据位置 Data position | 数据内容 Content of data |
|-----------------------|-------------------------------|
| 1--8 | 模块批次号 Module batch number |
| 9--12 | 模块序列号 Module serial number |

最大额定值
Absolute Maximum Ratings

| 符号 Symbol | 参数名称 Parameter | 测试条件 Test Conditions | 数值 Value | 单位 Unit |
|--------------|--|--|-------------|------------|
| V_{CES} | 集电极-发射极电压 Collector-emitter voltage | $V_{GE} = 0V, T_C = 25^\circ C$ | 750 | V |
| V_{GES} | 栅极-发射极电压 Gate-emitter voltage | $T_C = 25^\circ C$ | ± 20 | V |
| I_C | 集电极电流 Collector-emitter current | $T_F = 80^\circ C, T_{vjmax} = 175^\circ C$ | 450 | A |
| | 额定电流 Rating Current | | 820 | A |
| $I_{C(RM)}$ | 集电极峰值电流 Peak collector current | $t_p = 1ms$ | 1640 | A |
| P_{max} | 晶体管部分最大损耗 Max. transistor power dissipation | $T_{vj} = 175^\circ C, T_C = 25^\circ C$ | 1111 | W |
| ρ_t | 二极管 ρ_t 值 Diode ρ_t | $V_R = 0V, t_p = 10ms, T_{vj} = 150^\circ C$ | 14.4 | kA^2s |
| V_{isol} | 绝缘电压(模块) Isolation voltage – per module | 短接所有端子，端子与基板间施加电压 (Commoned terminals to baseplate), AC RMS, 1 min, 50Hz, $T_C = 25^\circ C$ | 2500 | V |

热和机械数据
Thermal & Mechanical Data

| 参数 Symbol | 说明 Explanation | 值 Value | 单位 Unit |
|--|--------------------------------|------------|------------|
| 爬电距离 Creepage distance | 端子-散热器 Terminal to heatsink | 9 | mm |
| | 端子-端子 Terminal to terminal | 9 | mm |
| 绝缘间隙 Clearance | 端子-散热器 Terminal to heatsink | 4.5 | mm |
| | 端子-端子 Terminal to terminal | 4.5 | mm |
| 相对漏电起痕指数 CTI (Comparative tracking index) | | >200 | |

热和机械数据
Thermal & Mechanical Data

| 符号 Symbol | 参数名称 Parameter | 测试条件 Test Conditions | 最小值 Min. | 典型值 Typ. | 最大值 Max. | 单位 Unit |
|---------------------|--|--|-------------|-------------|-------------|------------------|
| $R_{th(J-F)}$ IGBT | IGBT 热阻 Thermal resistance – IGBT | 冷却液: 50%乙二醇溶液; $\Delta V/\Delta t=10 \text{ dm}^3/\text{min}$; $T_F = 75 \text{ }^\circ\text{C}$ Cooling Fluid: 50% water / 50% ethylenglycol; $\Delta V/\Delta t=10 \text{ dm}^3/\text{min}$; $T_F= 75 \text{ }^\circ\text{C}$ | | 115 | 135 | K / kW |
| $R_{th(J-F)}$ Diode | 二极管热阻 Thermal resistance – Diode | | | 160 | 180 | K / kW |
| ΔP | 冷却液流阻 Pressure drop in cooling circuit | 冷却液: 50%乙二醇溶液; $\Delta V/\Delta t=10 \text{ dm}^3/\text{min}$; $T_F = 25 \text{ }^\circ\text{C}$ Cooling Fluid: 50% water / 50% ethylenglycol; $\Delta V/\Delta t=10 \text{ dm}^3/\text{min}$; $T_F= 25 \text{ }^\circ\text{C}$ | | 68 | | mbar |
| P | 冷却液最大压力 Maximum pressure in cooling circuit | | | | 2 | bar |
| $T_{vj op}$ | 工作结温 Operating junction temperature | IGBT 部分 (IGBT) | -40 150 | | 150 175 | $^\circ\text{C}$ |
| | | 二极管部分 (Diode) | -40 150 | | 150 175 | $^\circ\text{C}$ |
| T_{stg} | 存储温度 Storage temperature range | | -40 | | 125 | $^\circ\text{C}$ |
| M | 安装力矩 Screw torque | 安装紧固用 - M4 Mounting - M4 | 1.8 | 2.0 | 2.2 | Nm |
| | | PCB 安装用 PCB Mounting | 0.55 | 0.6 | 0.65 | Nm |

热敏电阻数据
NTC-Thermistor Data

| 符号 Symbol | 参数名称 Parameter | 测试条件 Test Conditions | 最小值 Min. | 典型值 Typ. | 最大值 Max. | 单位 Unit |
|--------------|--|--|-------------|-------------|-------------|------------|
| R_{25} | 额定电阻值 Rated resistance | $T_C = 25 \text{ }^\circ\text{C}$ | | 5 | | k Ω |
| $\Delta R/R$ | R_{100} 偏差 Deviation of R_{100} | $T_C = 100 \text{ }^\circ\text{C}$, $R_{100}=493\Omega$ | -5 | | 5 | % |
| P_{25} | 耗散功率 Power dissipation | $T_C = 25 \text{ }^\circ\text{C}$ | | | 20 | mW |
| $B_{25/50}$ | B-值 B-value | $R_2 = R_{25} \exp [B_{25/50}(1/T_2 - 1/(298.15 \text{ K}))]$ | | 3375 | | K |
| $B_{25/80}$ | B-值 B-value | $R_2 = R_{25} \exp [B_{25/80}(1/T_2 - 1/(298.15 \text{ K}))]$ | | 3411 | | K |
| $B_{25/100}$ | B-值 B-value | $R_2 = R_{25} \exp [B_{25/100}(1/T_2 - 1/(298.15 \text{ K}))]$ | | 3433 | | K |

Caution: This device is sensitive to electrostatic discharge. Users should follow ESD handling procedures.

注意: 该器件对静电敏感, 用户须采取 ESD 防护措施。

电特性值
Electrical Characteristics

 除非特别声明，否则 $T_C = 25\text{ }^\circ\text{C}$
 $T_C = 25\text{ }^\circ\text{C}$ unless otherwise stated

| 符号 Symbol | 参数名称 Parameter | 条件 Test Conditions | 最小值 Min. | 典型值 Typ. | 最大值 Max. | 单位 Unit |
|----------------------|---|---|-------------|-------------|-------------|---------------|
| I_{CES} | 集电极截止电流 Collector cut-off current | $V_{GE} = 0V, V_{CE} = V_{CES}$ | | | 1 | mA |
| | | $V_{GE} = 0V, V_{CE} = V_{CES}, T_C = 150\text{ }^\circ\text{C}$ | | | 10 | mA |
| | | $V_{GE} = 0V, V_{CE} = V_{CES}, T_C = 175\text{ }^\circ\text{C}$ | | | 15 | mA |
| I_{GES} | 栅极漏电流 Gate leakage current | $V_{GE} = \pm 20V, V_{CE} = 0V$ | | | 0.5 | μA |
| $V_{GE(TH)}$ | 栅极-发射极阈值电压 Gate threshold voltage | $I_C = 15\text{mA}, V_{GE} = V_{CE}$ | 5.30 | 5.90 | 6.50 | V |
| $V_{CE(sat)}^{(*1)}$ | 集电极-发射极饱和电压 Collector-emitter saturation voltage | $V_{GE} = 15V, I_C = 450A$ | | 1.25 | 1.55 | V |
| | | $V_{GE} = 15V, I_C = 450A, T_{vj} = 150\text{ }^\circ\text{C}$ | | 1.30 | | V |
| | | $V_{GE} = 15V, I_C = 450A, T_{vj} = 175\text{ }^\circ\text{C}$ | | 1.30 | | V |
| | | $V_{GE} = 15V, I_C = 820A$ | | 1.60 | | V |
| I_F | 二极管正向直流电流 Diode forward current | DC | | 450 | | A |
| | 二极管额定正向电流 Diode rating forward current | | | 820 | | A |
| I_{FRM} | 二极管正向重复峰值电流 Diode peak forward current | $t_p = 1\text{ms}$ | | 1640 | | A |
| $V_F^{(*1)}$ | 二极管正向电压 Diode forward voltage | $I_F = 450A, V_{GE} = 0$ | | 1.65 | 1.95 | V |
| | | $I_F = 450A, V_{GE} = 0, T_{vj} = 150\text{ }^\circ\text{C}$ | | 1.65 | | V |
| | | $I_F = 450A, V_{GE} = 0, T_{vj} = 175\text{ }^\circ\text{C}$ | | 1.65 | | V |
| | | $I_F = 820A, V_{GE} = 0$ | | 2.05 | | V |
| I_{SC} | 短路电流 Short circuit current | $T_{vj} = 150\text{ }^\circ\text{C}, V_{CC} = 400V,$ $V_{GE} \leq 15V, t_p \leq 6\mu\text{s},$ $V_{CE(max)} = V_{CES} - L^{(*2)} \times di/dt,$ IEC 6074-9 | | 3800 | | A |

注意: 1. (*1) 表示该参数的测试点为辅助母排端子 (*1) indicates it is measured at the auxiliary busbar terminal),

Note: 2. (*2) 表示 L 是电路杂散电感加上 L_M (*2) indicates L is the circuit stray inductance plus L_M).

电特性值
Electrical Characteristics

 除非特别声明，否则 $T_C = 25\text{ }^\circ\text{C}$
 $T_C = 25\text{ }^\circ\text{C}$ unless otherwise stated

| 符号 Symbol | 参数名称 Parameter | 条件 Test Conditions | 最小值 Min. | 典型值 Typ. | 最大值 Max. | 单位 Unit |
|--------------|--|---|-------------|-------------|-------------|------------|
| C_{ies} | 输入电容 Input capacitance | $V_{CE} = 25V, V_{GE} = 0V, f = 100kHz$ | | 74 | | nF |
| Q_g | 栅极电荷 Gate charge | $\pm 15V$ | | 4.20 | | μC |
| C_{res} | 反向传输电容 Reverse transfer capacitance | $V_{CE} = 25V, V_{GE} = 0V, f = 100kHz$ | | 0.29 | | nF |
| L_M | 模块电感 Module inductance | | | 8 | | nH |
| R_{INT} | 内阻 Internal transistor resistance | | | 0.5 | | m Ω |

电特性值
Electrical Characteristics

| 符号 Symbol | 参数名称 Parameter | 测试条件 Test Conditions | 最小值 Min. | 典型值 Typ. | 最大值 Max. | 单位 Unit |
|--------------|---|---|------------------------|-------------|-------------|------------|
| $t_{d(off)}$ | 关断延迟时间 Turn-off delay time | $I_C = 450A,$ $V_{CE} = 400V,$ $V_{GE} = \pm 15V,$ $R_{G(OFF)} = 5.1\Omega,$ $L_S = 55nH,$ $dv/dt = 4400V/us$ ($T_{vj} = 150^\circ C$). | $T_{vj} = 25^\circ C$ | 1065 | | ns |
| | | | $T_{vj} = 150^\circ C$ | 1080 | | |
| | | | $T_{vj} = 175^\circ C$ | 1095 | | |
| t_f | 下降时间 Fall time | | $T_{vj} = 25^\circ C$ | 80 | | ns |
| | | | $T_{vj} = 150^\circ C$ | 85 | | |
| | | | $T_{vj} = 175^\circ C$ | 90 | | |
| E_{OFF} | 关断损耗 Turn-off energy loss | | $T_{vj} = 25^\circ C$ | 33 | | mJ |
| | | | $T_{vj} = 150^\circ C$ | 36 | | |
| | | | $T_{vj} = 175^\circ C$ | 37 | | |
| $t_{d(on)}$ | 开通延迟时间 Turn-on delay time | $T_{vj} = 25^\circ C$ | | 845 | ns | |
| | | $T_{vj} = 150^\circ C$ | | 850 | | |
| | | $T_{vj} = 175^\circ C$ | | 855 | | |
| t_r | 上升时间 Rise time | $T_{vj} = 25^\circ C$ | | 87 | ns | |
| | | $T_{vj} = 150^\circ C$ | | 105 | | |
| | | $T_{vj} = 175^\circ C$ | | 105 | | |
| E_{ON} | 开通损耗 Turn-on energy loss | $T_{vj} = 25^\circ C$ | | 10.0 | mJ | |
| | | $T_{vj} = 150^\circ C$ | | 10.5 | | |
| | | $T_{vj} = 175^\circ C$ | | 11.0 | | |
| Q_{rr} | 二极管反向恢复电荷 Diode reverse recovery charge | $T_{vj} = 25^\circ C$ | | 47 | μC | |
| | | $T_{vj} = 150^\circ C$ | | 52 | | |
| | | $T_{vj} = 175^\circ C$ | | 57 | | |
| I_{rr} | 二极管反向恢复电流 Diode reverse recovery current | $T_{vj} = 25^\circ C$ | | 320 | A | |
| | | $T_{vj} = 150^\circ C$ | | 335 | | |
| | | $T_{vj} = 175^\circ C$ | | 345 | | |
| E_{rec} | 二极管反向恢复损耗 Diode reverse recovery energy | $T_{vj} = 25^\circ C$ | | 15.5 | mJ | |
| | | $T_{vj} = 150^\circ C$ | | 17.0 | | |
| | | $T_{vj} = 175^\circ C$ | | 18.5 | | |

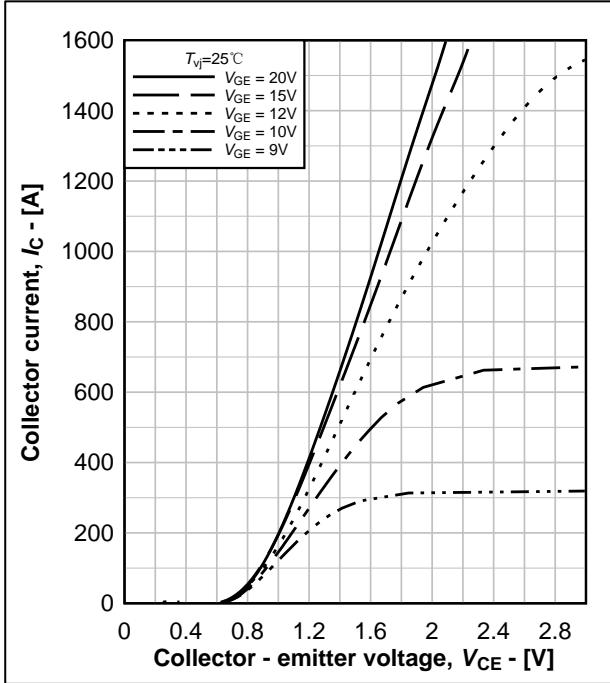


图 3. IGBT 输出特性典型曲线, $I_C = f(V_{CE})$

Fig.3 Typical IGBT output characteristics, $I_C = f(V_{CE})$

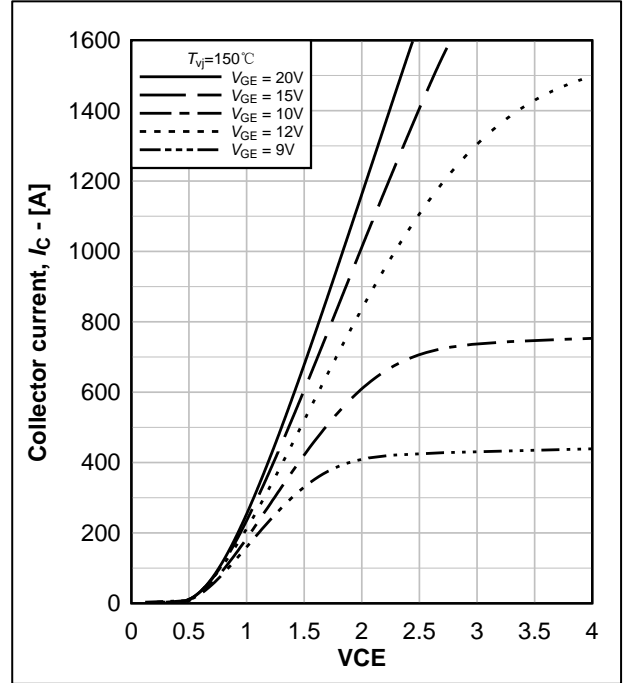


图 4. IGBT 输出特性典型曲线, $I_C = f(V_{CE})$

Fig.4 Typical IGBT output characteristics, $I_C = f(V_{CE})$

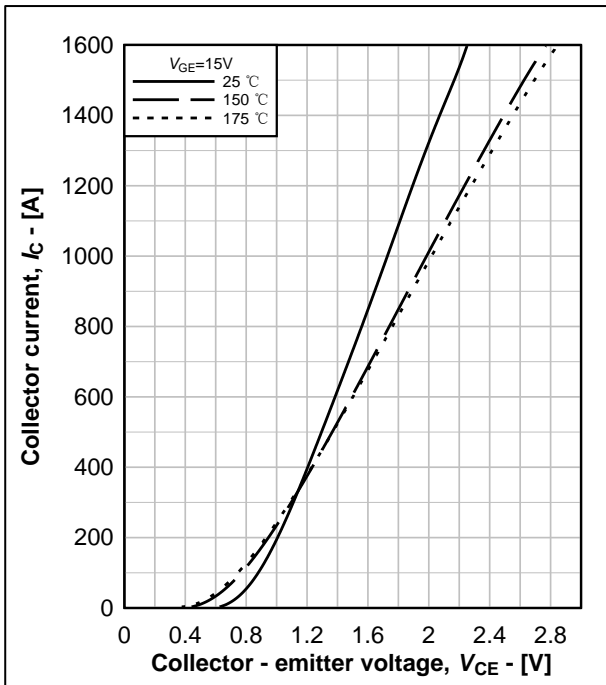


图 5. IGBT 输出特性典型曲线, $I_C = f(V_{CE})$

Fig.5 Typical IGBT output characteristics, $I_C = f(V_{CE})$

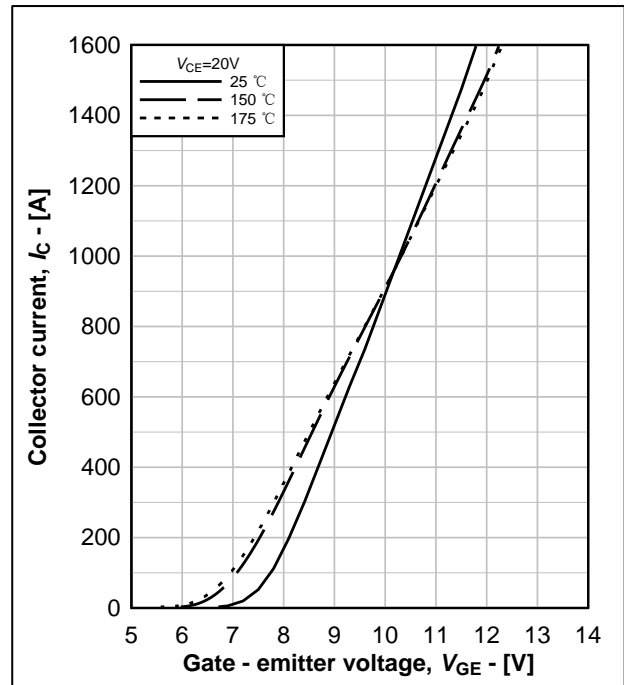


图 6. IGBT 传输特性典型曲线, $I_C = f(V_{GE})$

Fig.6 Typical IGBT transfer characteristics, $I_C = f(V_{GE})$

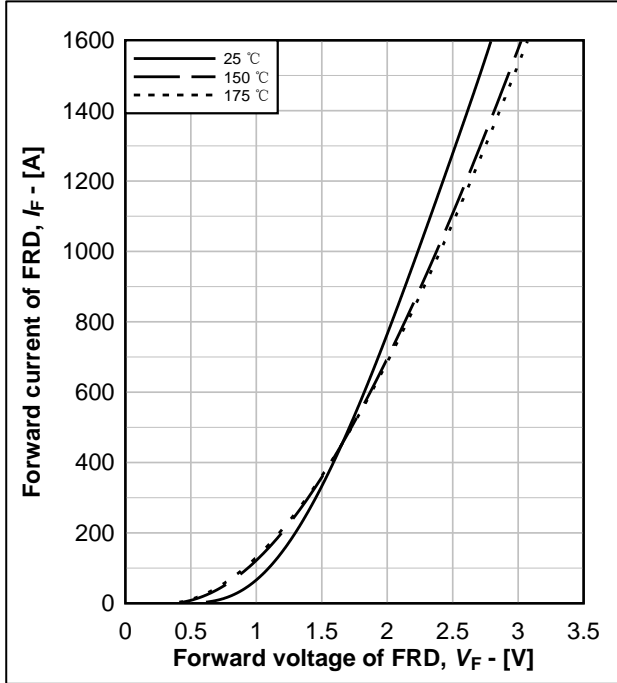

 图 7. FRD 输出特性典型曲线, $I_F = f(V_F)$

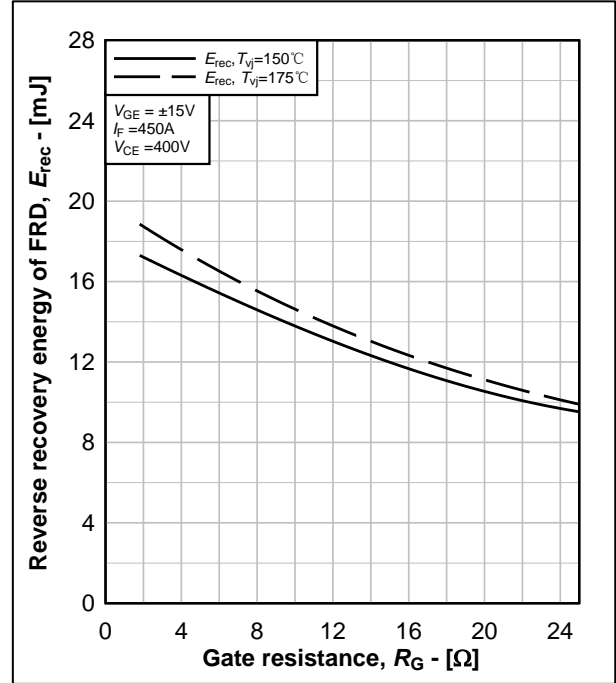
 Fig.7 Typical FRD output characteristics, $I_F = f(V_F)$

 图 8. FRD 反向恢复能耗典型曲线, $E_{rec} = f(R_G)$

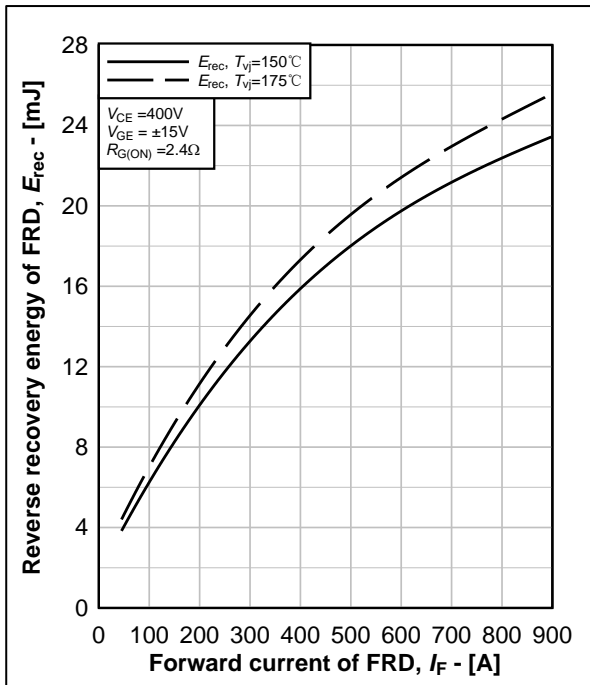
 Fig.8 Typical FRD E_{rec} , $E_{rec} = f(R_G)$

 图 9. FRD 反向恢复能耗典型曲线, $E_{rec} = f(I_F)$

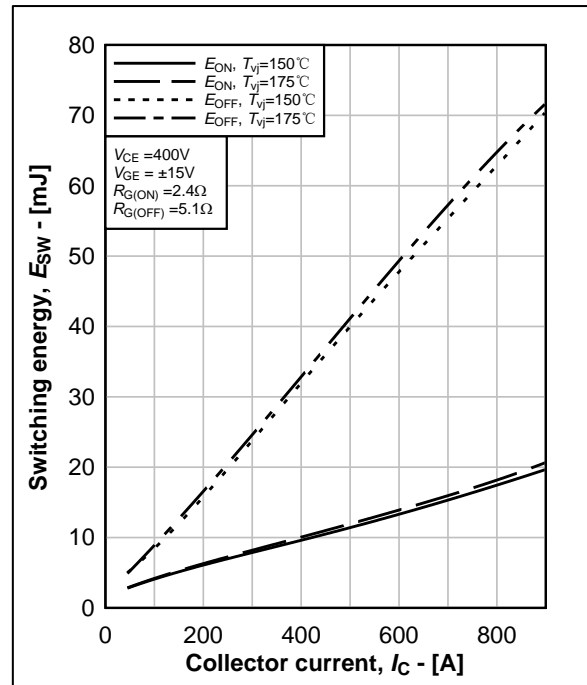
 Fig.9 Typical FRD E_{rec} , $E_{rec} = f(I_F)$

 图 10. IGBT 开关能耗典型曲线, $E_{on} = f(I_C)$, $E_{off} = f(I_C)$

 Fig.10 Typical IGBT switching energy, $E_{on} = f(I_C)$, $E_{off} = f(I_C)$

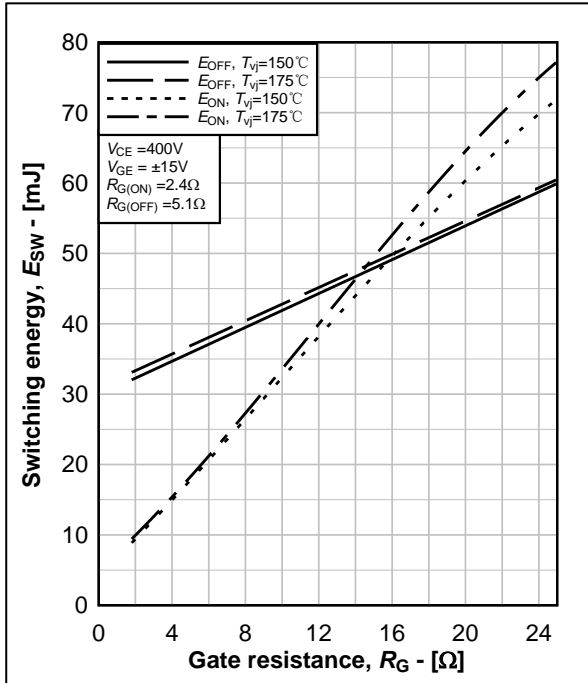

 图 11. IGBT 开关能耗典型曲线, $E_{on}=f(R_G)$, $E_{off}=f(R_G)$

Fig.11 Typical IGBT switching energy,

$$E_{on}=f(R_G), E_{off}=f(R_G)$$

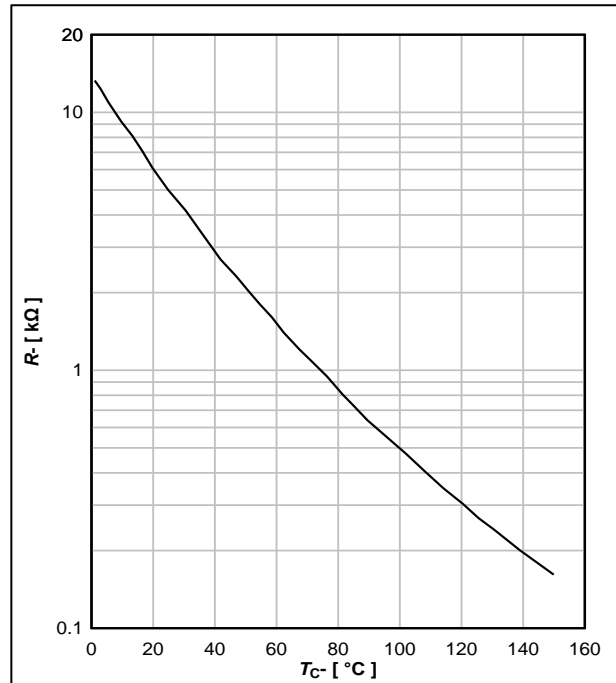

 图 12. 热敏电阻典型特性曲线, $R=f(T_C)$

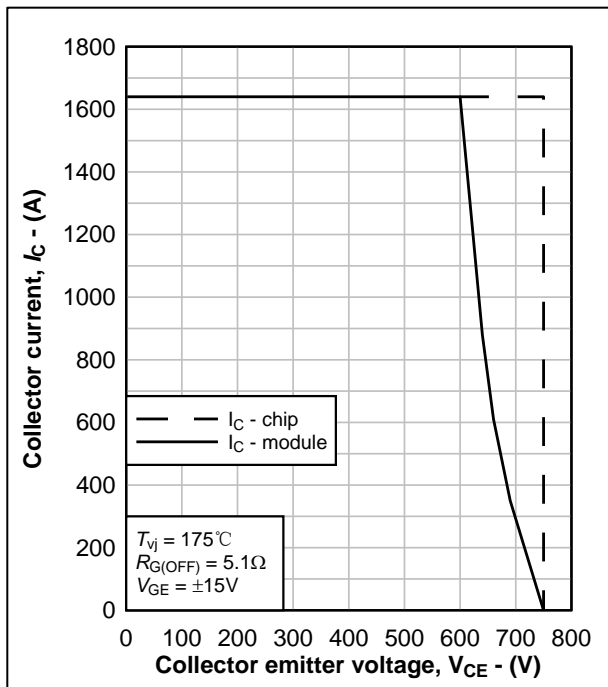
 Fig.12 Typical NTC thermistor characteristic, $R=f(T_C)$

 图 13. IGBT 反偏安全工作区, $I_C=f(V_{CE})$

Fig.13 Reverse bias safe operating area of IGBT,

$$I_C=f(V_{CE})$$

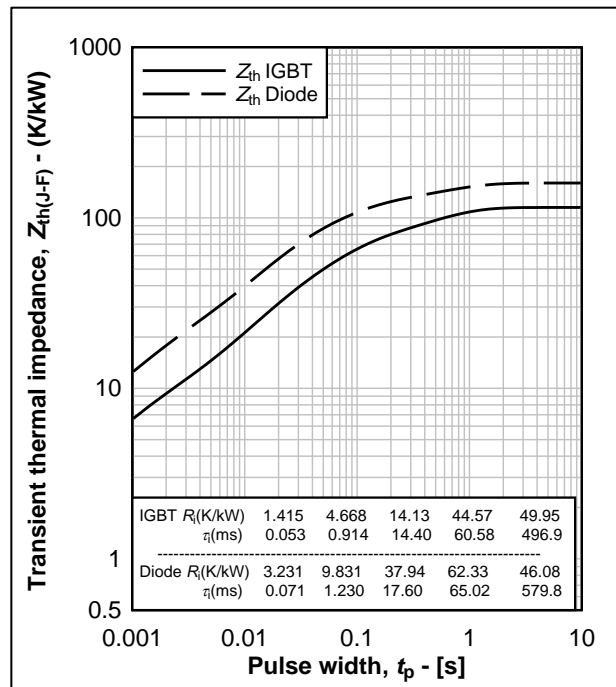
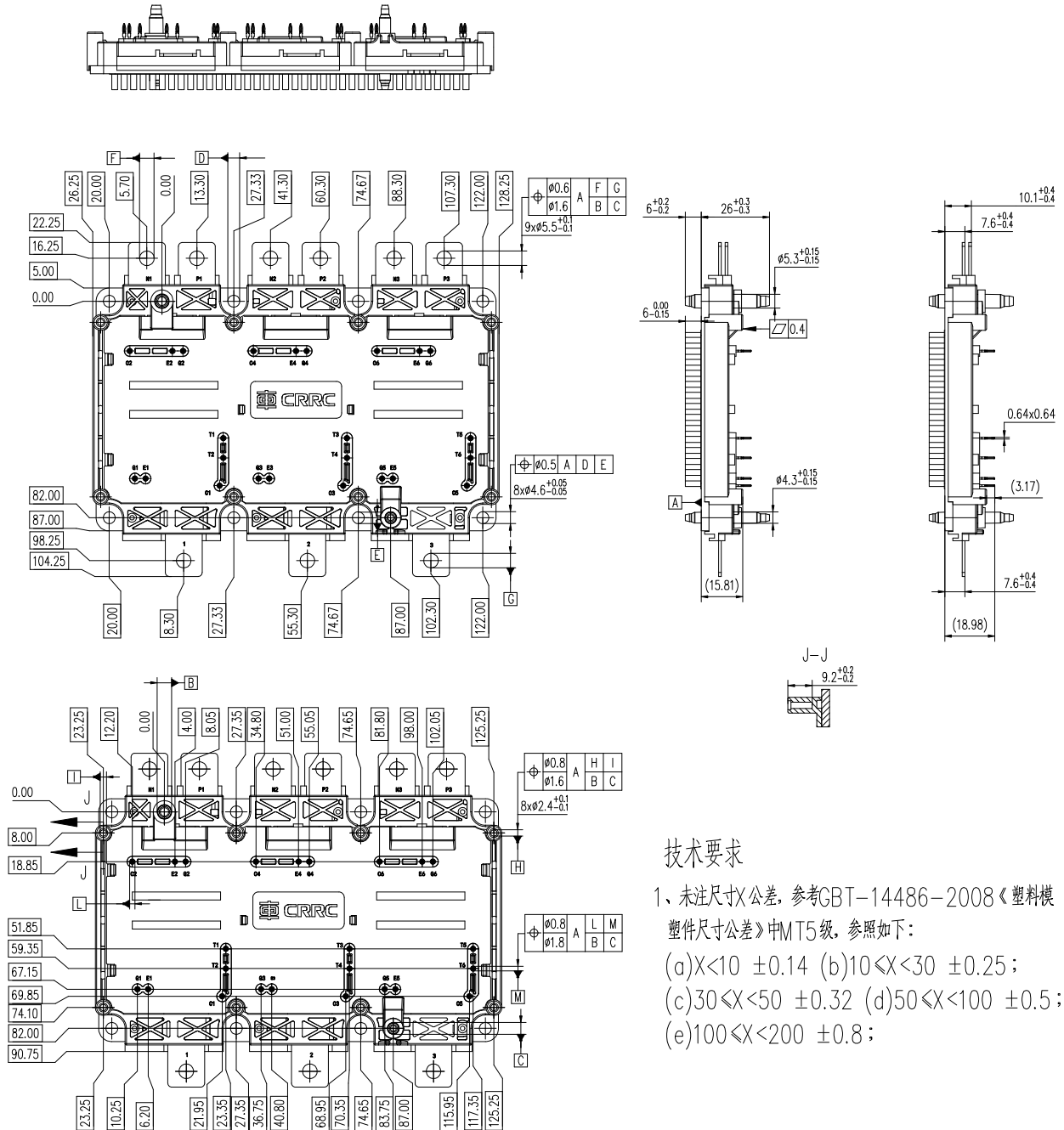

 图 14. 瞬态热阻抗曲线, $Z_{th(J-F)}=f(t_p)$

 Fig.14 Transient thermal impedance, $Z_{th(J-F)}=f(t_p)$



重量 Weight: 735g 模块外观类型 Module outline code: S3

图 15. 模块外观尺寸

Fig. 15 Module outlines

株洲中车时代半导体有限公司

ZHUZHOU CRRC TIMES SEMICONDUCTOR CO., LTD.

| | | | |
|------|-----------|---|---|
| 地 址 | Address | 湖南省株洲市石峰区田心工业园 | Tianxin Industrial Park, Shifeng District, ZhuZhou City, Hunan Province, China |
| 邮 编 | Zipcode | 412001 | |
| 电 话 | Telephone | +86 (0)731-28498268, 28498238, 28493472 | |
| 传 真 | Fax | +86 (0)731-28498851, 28498494 | |
| 电子邮箱 | Email | sbu@crzczic.cc | |
| 网 址 | Web Site | http://www.sbu.crzczic.cc | |

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- (4) During the application, if the working conditions are beyond the limitation of temperature, voltage, current or safe operating area of the product defined in the product datasheet, our company cannot guarantee the reliability of the product.
- (5) When the products are in use, it is strictly prohibited to touch. After power off, to ensure that there is no residual charge and the products have been cooled before they can be touched. And all operations must be under ESD protection measures.
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